

PIMP32-Q

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k Ω , R2 = 10 k Ω

16 February 2022

Product data sheet

1. General description

PNP/PNP Resistor-Equipped double Transistor (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PIMN32-Q NPN/PNP complement: PIMC32-Q

2. Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Digital applications
- · Cost-saving alternative to BC807-Q series in digital applications
- · Control of IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	-50	V	
Io	output current			-	-	-500	mA	
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ	
R2/R1	bias resistor ratio		[1]	4.1	4.55	5		

[1] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	<u> </u>	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0 H1 H2 H3	TR1 R2 R1
6	O1	output (collector) TR1	SC-74; TSOP6 (SOT457)	
				GND1 I1 O2 aaa-019790

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PIMP32-Q	SC-74; TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PIMP32-Q	4 J

8. Limiting values

Table 5. Limiting values

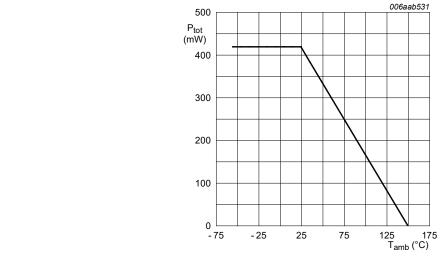
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or					-
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
VI	input voltage			-12	5	V
I _O	output current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	290	mW
Per device						'
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	420	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

 $^{[1] \}quad \text{Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, } 35~\mu\text{m copper, tin-plated and standard footprint.}$

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50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k Ω , R2 = 10 k Ω



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

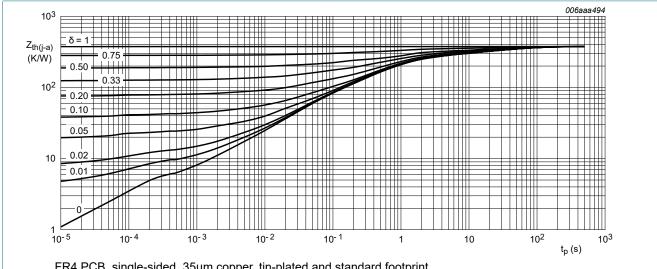
Fig. 1. Per device: Power derating curve

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	432	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W	
Per device								
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	298	K/W	

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35µm copper, tin-plated and standard footprint

Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; Fig. 2. typical values

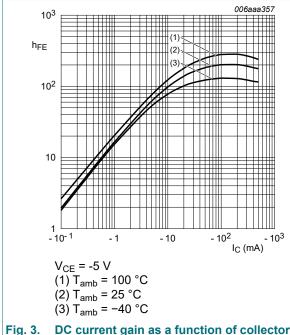
50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k Ω , R2 = 10 k Ω

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
$V_{(BR)CBO}$	collector-base breakdown voltage	I _C = -100 μA; I _E = 0 A; T _{amb} = 25 °C		-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -50 V; I _B = 0 A; T _{amb} = 25 °C		-	-	-0.5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-0.65	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		70	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -50 mA; I_B = -2.5 mA; T_{amb} = 25 °C		-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}; T_{amb} = 25 ^{\circ}\text{C}$		-0.4	-0.65	-1	V
$V_{I(on)}$	on-state input voltage	V_{CE} = -0.3 V; I_{C} = -20 mA; T_{amb} = 25 °C		-0.5	-0.95	-1.4	V
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	4.1	4.55	5	
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	11	-	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	140	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor





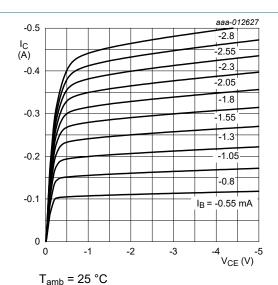


Fig. 4. Collector current as a function of collectoremitter voltage, typical values

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k Ω , R2 = 10 k Ω

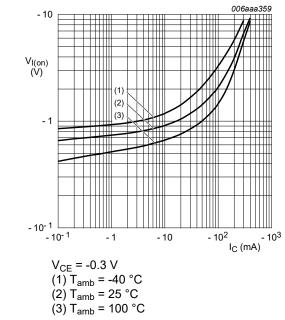
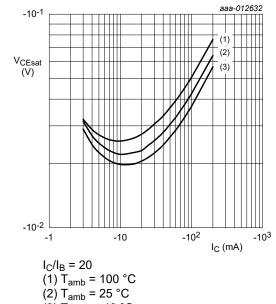
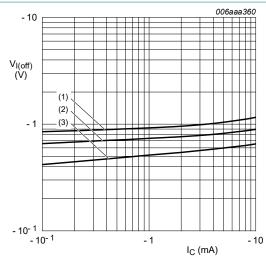


Fig. 5. On-state input voltage as a function of collector | Fig. 6. current; typical values



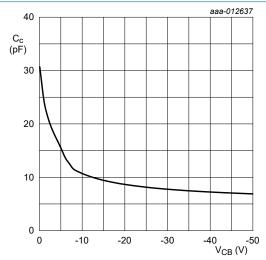
(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

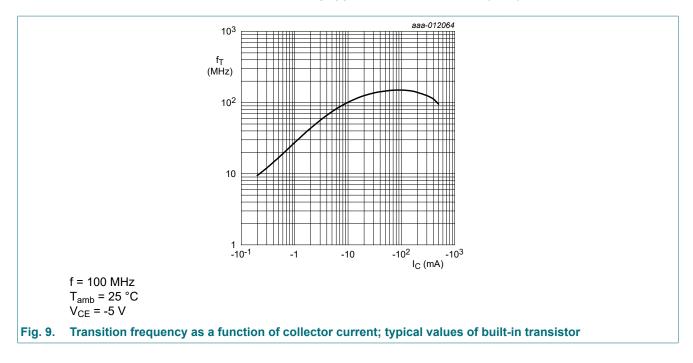
Off-state input voltage as a function of collector current; typical values



f = 1 MHz $T_{amb} = 25 \, ^{\circ}C$

Fig. 8. Collector capacitance as a function of collectorbase voltage; typical values

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11. Test information

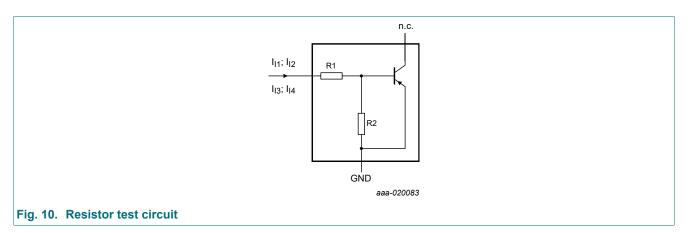
Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$



Resistor test conditions

Table 8. Resistor test conditions

R1 (kΩ)	R2 (kΩ)	Test conditions	Test conditions				
		I _{I1}	I ₁₂	I ₁₃	I ₁₄		
2.2	10	-0.7 mA	-0.8 mA	0.45 mA	0.55 mA		

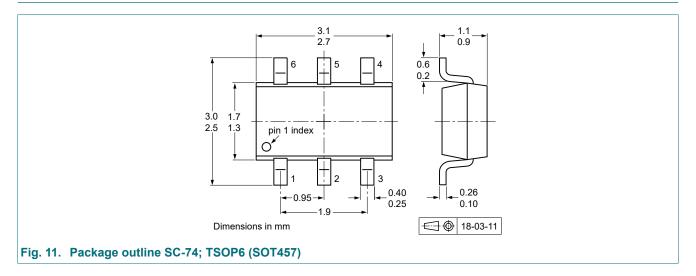
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

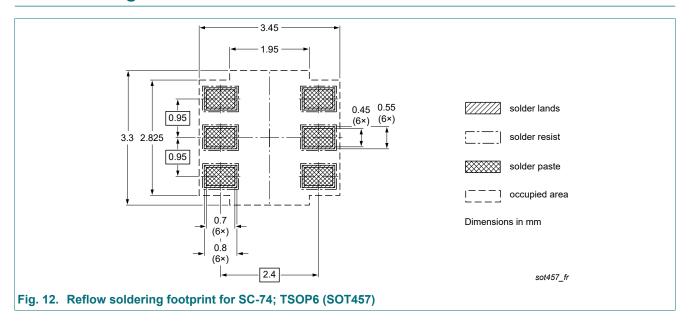
PIMP32-Q

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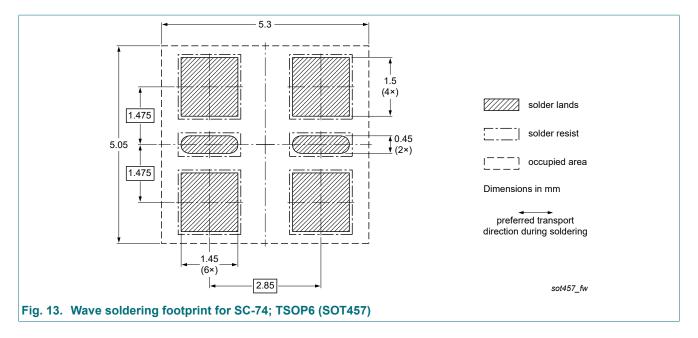
12. Package outline



13. Soldering



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14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMP32-Q v.1	20220216	Product data sheet	-	-

50 V, 500 mA PNP/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k Ω , R2 = 10 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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